TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP421

Office Equipment
Household Appliances
Solid State Relays
Switching Power Supplies
Various Controllers

Signal Transmission Between Different Voltage Circuits

The TOSHIBA TLP421 consists of a silicone photo—transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP (DIP4) with having high isolation voltage (AC: 5kV_{RMS} (min)).

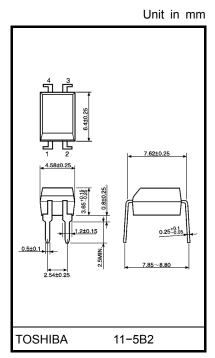
- Collector-emitter voltage: 80V (min.)
- \bullet Current transfer ratio: 50% (min.)

Rank GB: 100% (min.)

- Isolation voltage: 5000V_{rms} (min.)
- UL recognized: UL1577
- BSI approved: BS EN60065: 2002

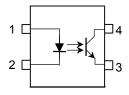
Approved no.8411 BS EN60950-1: 2002 Approved no.8412

SEMKO approved: EN60065, EN60950, EN60335
 Approved no.9910249/01



Weight: 0.26 g

Pin Configurations (top view)



1: Anode

2: Cathode

3: Emitter

4 : Collector



• Option(D4)type

TÜV approved: DIN EN 60747-5-2

Approved no. R9950202

Maximum operating insulation voltage: $890 V_{PK}$ Maximum permissible overvoltage: $8000 V_{PK}$

(Note): When a EN 60747-5-2 approved type is needed, please designate the "Option(D4)"

Making the VDE application: DIN EN 60747-5-2

• Construction mechanical rating

	7.62mm Pitch Typical Type	10.16mm Pitch TLPxxxF Type
Creepage distance	7.0mm(min)	8.0mm(min)
Clearance	7.0mm(min)	8.0mm(min)
Insulation thickness	0.4mm(min)	0.4mm(min)

Current Transfer Ratio

Туре	Classi– fication (*1)	Current Transfer Ratio (%) (I _C / I _F) I _F = 5mA, V _{CE} = 5V, Ta = 25°C		Marking Of Classification			
		Min Max					
	(None)	50 600		Blank, Y, Y+, G, G+, B, B+, GB			
	Rank Y	50	150	Y, Y+			
TLP421	Rank GR	100	300	G, G+			
	Rank BL	200	600	B, B+			
	Rank GB	100	600	G, G+, B, B+, GB			

(*1): Ex. rank GB: TLP421 (GB)

(Note): Application type name for certification test, please use standard product type name, i. e. TLP421 (GB): TLP421

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
	Forward current		l _F	60	mA
	Forward current derating(Ta ≥ 39°C)		ΔI _F / °C	-0.7	mA / °C
	Pulse forward current	(Note 2)	I _{FP}	1	А
LED	Power dissipation		P _D	100	mW
	Power dissipation derating		ΔP _D / °C	-1.0	mW / °C
	Reverse voltage		V _R	5	V
	Junction temperature		Тj	125	°C
	Collector-emitter voltage		V _{CEO}	80	V
	Emitter-collector voltage		V _{ECO}	7	V
tor	Collector current		Ic	50	mA
Detector	Power dissipation(single circuit)		PC	150	mW
	Power dissipation derating (Ta ≥ 25°C)(single circuit)		ΔP _C / °C	-1.5	mW / °C
	Junction temperature		Tj	125	°C
Оре	rating temperature range		T _{opr}	-55~100	°C
Stor	age temperature range		T _{stg}	-55~125	°C
Lea	d soldering temperature (10s)		T _{sol}	260	°C
Tota	l package power dissipation		P _T	250	mW
	ll package power dissipation derating ≥ 25°C)		ΔP _T / °C	-2.5	mW / °C
Isola	ation voltage	(Note 3)	BV_S	5000	V _{rms}

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 2): 100µs pulse, 100Hz frequency

(Note 3): AC, 1 min., R.H.≤ 60%. Apply voltage to LED pin and detector pin together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Тур.	Max	Unit
Supply voltage	V _{CC}	_	5	24	٧
Forward current	lF	_	16	25	mA
Collector current	IC	_	1	10	mA
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	V_{F}	I _F = 10 mA	1.0	1.2	1.3	V
ΓED	Reverse current	I _R	V _R = 5 V	1	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	1	V
J.	Emitter-collector breakdown voltage	V _(BR) ECO	I _E = 0.1 mA	7	_	-	٧
Detector	Collector dark current	l=(l===)	V _{CE} = 24 V (ambient light below 1000 ℓx)	_	0.01 (0.1)	0.1 (10)	μΑ
	Collector dark current I _D (I _{CEO})	V _{CE} = 24 V (ambient light Ta = 85°C below 1000 ℓx)	-	0.6 (1)	50 (50)	μΑ	
	Capacitance (collector to emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition		MIn	Тур.	Max	Unit
Current transfer ratio	lo / le	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$		50	-	600	%
Current transfer fatto	10714		Rank GB	100	ı	600	70
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, V _{CE} = 0.4 V		_	60	1	%
			Rank GB	30	ı	1	/0
		I _C = 2.4 mA, I _F = 8 mA		_	_	0.4	
Collector–emitter saturation voltage	V _{CE (sat)}	I _C = 0.2 mA, I _F = 1 mA		_	0.2		V
			Rank GB	_	_	0.4	

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	_	_	V _{rms}
		AC, 1 second, in oil	_	10000	_	vrms
		DC, 1 minute, in oil	_	10000		Vdc

Switching Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Rise time	t _r		_	2	_	
Fall time	t _f	V _{CC} = 10 V, I _C = 2 mA	_	3	_	110
Turn-on time	t _{on}	$R_L = 100\Omega$	_	3	_	μs
Turn-off time	t _{off}		_	3	_	
Turn-on time	t _{ON}		_	2	_	
Storage time	t _S	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	_	25	_	μs
Turn-off time	t _{OFF}		_	50	_	

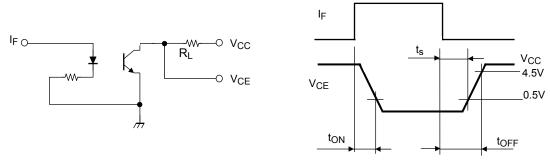
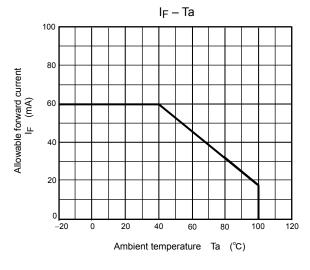
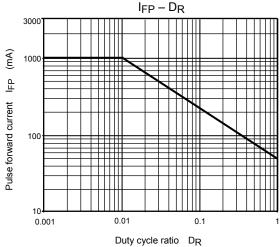
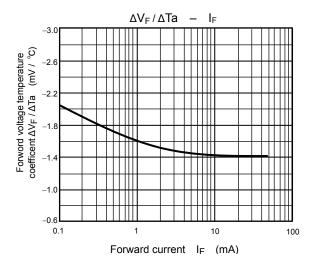
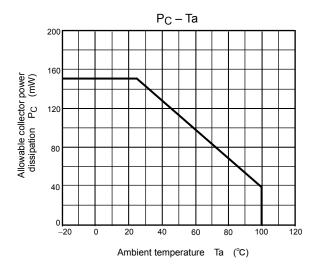


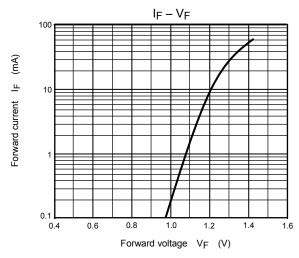
Fig.1 Switching time test circuit

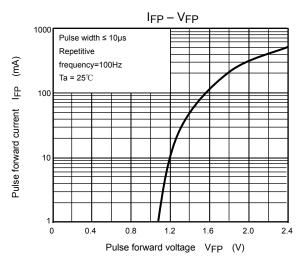




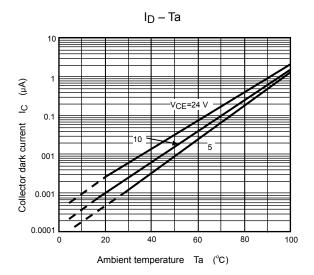


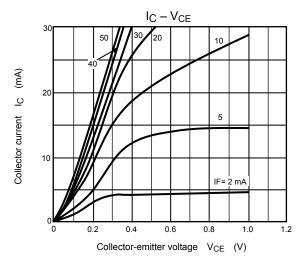


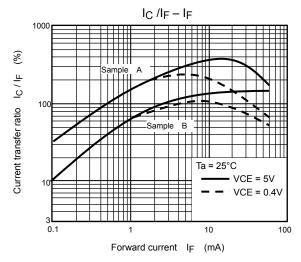


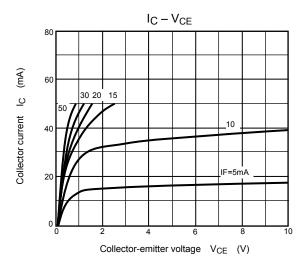


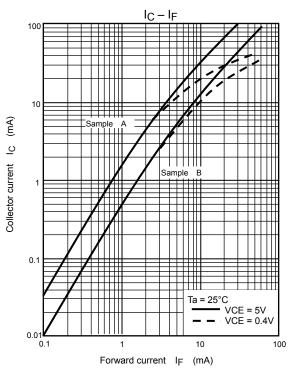
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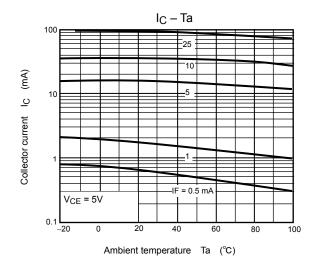


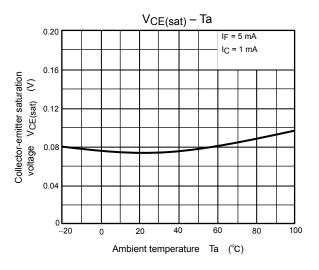


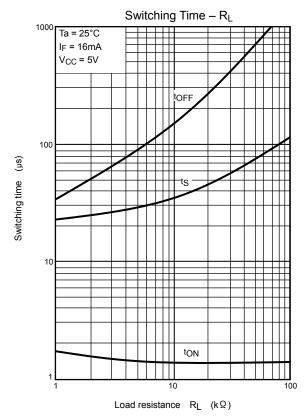












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